# MTP75N03HDL

**Preferred Device**

# Power MOSFET
# 75 Amps, 25 Volts, Logic Level
## N−Channel TO−220

This Power MOSFET is designed to withstand high energy in the avalanche and commutation modes. The energy efficient design also offers a drain−to−source diode with a fast recovery time. Designed for low−voltage, high−speed switching applications in power supplies, converters and PWM motor controls, and inductive loads. The avalanche energy capability is specified to eliminate the guesswork in designs where inductive loads are switched, and to offer additional safety margin against unexpected voltage transients.

- SPICE Parameters Available
- Diode is Characterized for Use in Bridge Circuits
- $I_{DSS}$ and $V_{DS(on)}$ Specified at Elevated Temperature
- Avalanche Energy Specified

**MAXIMUM RATINGS** ($T_C$ = 25°C unless otherwise noted)

| Rating | Symbol | Value | Unit |
|---|---|---|---|
| Drain−Source Voltage | $V_{DSS}$ | 25 | Vdc |
| Drain−Gate Voltage ($R_{GS}$ = 1.0 MΩ) | $V_{DGR}$ | 25 | Vdc |
| Gate−Source Voltage<br>− Continuous<br>− Single Pulse ($t_p \le 10$ ms) | $V_{GS}$ | <br>± 15<br>± 20 | <br>Vdc<br>Vpk |
| Drain Current − Continuous<br>− Continuous @ 100°C<br>− Single Pulse ($t_p \le 10$ μs) | $I_D$<br>$I_D$<br>$I_{DM}$ | 75<br>59<br>225 | Adc<br>Adc<br>Apk |
| Total Power Dissipation<br>Derate above 25°C | $P_D$ | 150<br>1.0 | Watts<br>W/°C |
| Operating and Storage Temperature Range | $T_J$, $T_{stg}$ | −55 to 175 | °C |
| Single Pulse Drain−to−Source Avalanche Energy − Starting $T_J$ = 25°C ($V_{DD}$ = 25 Vdc, $V_{GS}$ = 5.0 Vdc, $I_L$ = 75 Apk, L = 0.1 mH, $R_G$ = 25 Ω) | $E_{AS}$ | 280 | mJ |
| Thermal Resistance<br>−Junction to Case<br>−Junction to Ambient | <br>$R_{\theta JC}$<br>$R_{\theta JA}$ | <br>1.0<br>62.5 | °C/W |
| Maximum Lead Temperature for Soldering Purposes, 1/8″ from case for 10 seconds | $T_L$ | 260 | °C |

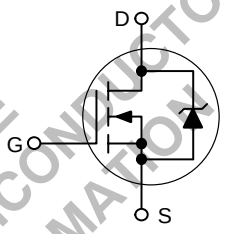


ON Semiconductor™

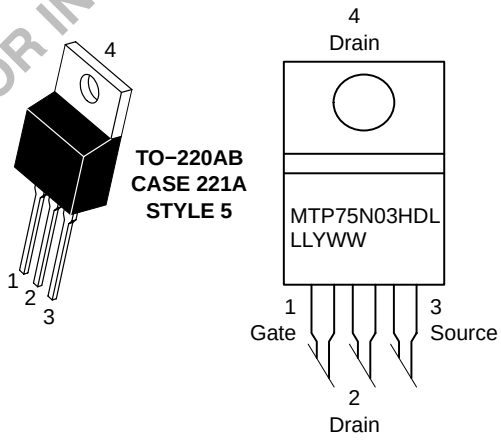
http://onsemi.com

**75 AMPERES**
**25 VOLTS**
**$R_{DS(on)}$ = 9 mΩ**

**N−Channel**




**MARKING DIAGRAM & PIN ASSIGNMENT**




**TO−220AB**
**CASE 221A**
**STYLE 5**




MTP75N03HDL = Device Code
LL = Location Code
Y = Year
WW = Work Week

**ORDERING INFORMATION**

| Device | Package | Shipping |
|---|---|---|
| MTP75N03HDL | TO−220AB | 50 Units/Rail |

**Preferred** devices are recommended choices for future use and best overall value.

**ELECTRICAL CHARACTERISTICS** ($T_J$ = 25°C unless otherwise noted)

| Characteristic | | Symbol | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| **OFF CHARACTERISTICS** | | | | | | |
| Drain−Source Breakdown Voltage ($C_{pk} \geq 2.0$) (Note 3.)<br>($V_{GS}$ = 0 Vdc, $I_D$ = 0.25 mA)<br>Temperature Coefficient (Positive) | | $V_{(BR)DSS}$ | 25 | − | − | Vdc<br><br>mV/°C |
| Zero Gate Voltage Drain Current<br>($V_{DS}$ = 25 Vdc, $V_{GS}$ = 0 Vdc)<br>($V_{DS}$ = 25 Vdc, $V_{GS}$ = 0 Vdc, $T_J$ = 125°C) | | $I_{DSS}$ | <br>−<br>− | <br>−<br>− | <br>100<br>500 | µAdc |
| Gate−Body Leakage Current ($V_{GS}$ = ± 20 Vdc, $V_{DS}$ = 0 V) | | $I_{GSS}$ | − | − | 100 | nAdc |
| **ON CHARACTERISTICS** (Note 1.) | | | | | | |
| Gate Threshold Voltage ($C_{pk} \geq 3.0$) (Note 3.)<br>($V_{DS}$ = $V_{GS}$, $I_D$ = 0.25 mA)<br>Temperature Coefficient (Negative) | | $V_{GS(th)}$ | 1.0 | 1.5 | 2.0 | Vdc<br><br>mV/°C |
| Static Drain−Source On−Resistance ($C_{pk} \geq 2.0$) (Note 3.)<br>($V_{GS}$ = 5.0 Vdc, $I_D$ = 37.5 Adc) | | $R_{DS(on)}$ | − | 6.0 | 9.0 | mΩ |
| Drain−Source On−Voltage ($V_{GS}$ = 10 Vdc)<br>($I_D$ = 75 Adc)<br>($I_D$ = 37.5 Adc, $T_J$ = 125°C) | | $V_{DS(on)}$ | <br>−<br>− | <br>−<br>− | <br>0.68<br>0.6 | Vdc |
| Forward Transconductance ($V_{DS}$ = 3.0 Vdc, $I_D$ = 20 Adc) | | $g_{FS}$ | 15 | 55 | − | mhos |
| **DYNAMIC CHARACTERISTICS** | | | | | | |
| Input Capacitance | ($V_{DS}$ = 25 Vdc, $V_{GS}$ = 0 Vdc, f = 1.0 MHz) | $C_{iss}$ | − | 4025 | 5635 | pF |
| Output Capacitance | | $C_{oss}$ | − | 1353 | 1894 | |
| Reverse Transfer Capacitance | | $C_{rss}$ | − | 307 | 430 | |
| **SWITCHING CHARACTERISTICS** (Note 2.) | | | | | | |
| Turn−On Delay Time | ($V_{DS}$ = 15 Vdc, $I_D$ = 75 Adc, $V_{GS}$ = 5.0 Vdc, $R_g$ = 4.7 Ω) | $t_{d(on)}$ | − | 24 | 48 | ns |
| Rise Time | | $t_r$ | − | 493 | 986 | |
| Turn−Off Delay Time | | $t_{d(off)}$ | − | 60 | 120 | |
| Fall Time | | $t_f$ | − | 149 | 300 | |
| Gate Charge | ($V_{DS}$ = 24 Vdc, $I_D$ = 75 Adc, $V_{GS}$ = 5.0 Vdc) | $Q_T$ | − | 61 | 122 | nC |
| | | $Q_1$ | − | 14 | 28 | |
| | | $Q_2$ | − | 33 | 66 | |
| | | $Q_3$ | − | 27 | 54 | |
| **SOURCE−DRAIN DIODE CHARACTERISTICS** | | | | | | |
| Forward On−Voltage | ($I_S$ = 75 Adc, $V_{GS}$ = 0 Vdc)<br>($I_S$ = 75 Adc, $V_{GS}$ = 0 Vdc, $T_J$ = 125°C) | $V_{SD}$ | <br>− | 0.97<br>0.87 | 1.1<br>− | Vdc |
| Reverse Recovery Time | ($I_S$ = 75 Adc, $V_{GS}$ = 0 Vdc, $dI_S/dt$ = 100 A/µs) | $t_{rr}$ | − | 58 | − | ns |
| | | $t_a$ | − | 27 | − | |
| | | $t_b$ | − | 30 | − | |
| Reverse Recovery Stored Charge | | $Q_{RR}$ | − | 0.088 | − | µC |

1. Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2%.
2. Switching characteristics are independent of operating junction temperature.
3. Reflects typical values. $C_{pk} = \left| \frac{\text{Max limit} - \text{Typ}}{3 \times \text{SIGMA}} \right|$

## TYPICAL ELECTRICAL CHARACTERISTICS

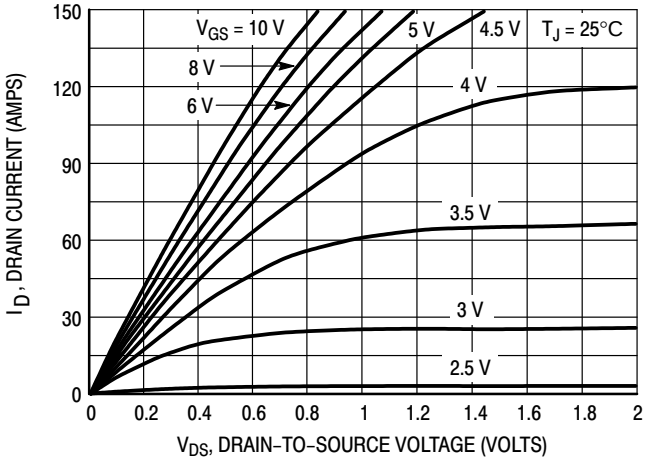



**Figure 1. On−Region Characteristics**

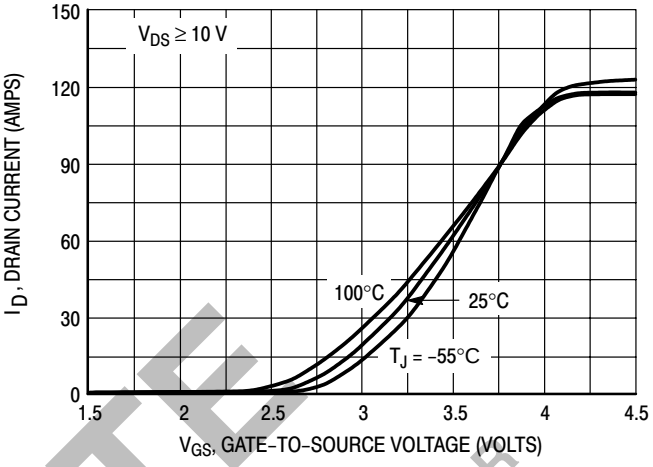



**Figure 2. Transfer Characteristics**

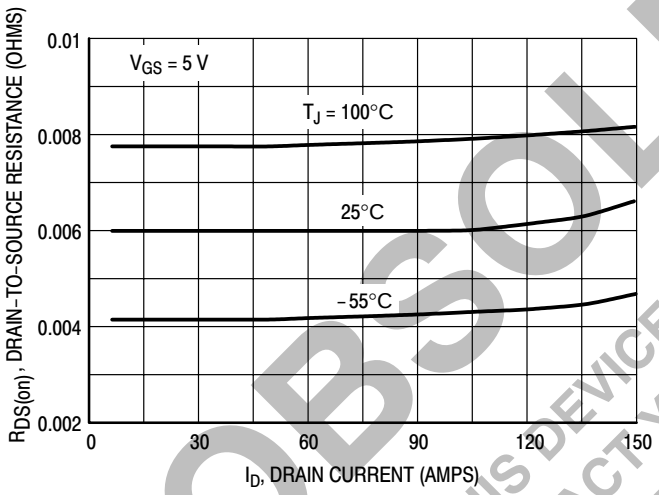



**Figure 3. On−Resistance versus Drain Current and Temperature**

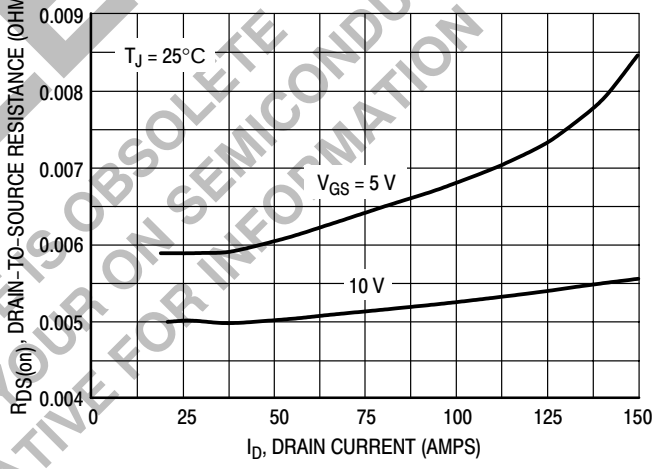



**Figure 4. On−Resistance versus Drain Current and Gate Voltage**

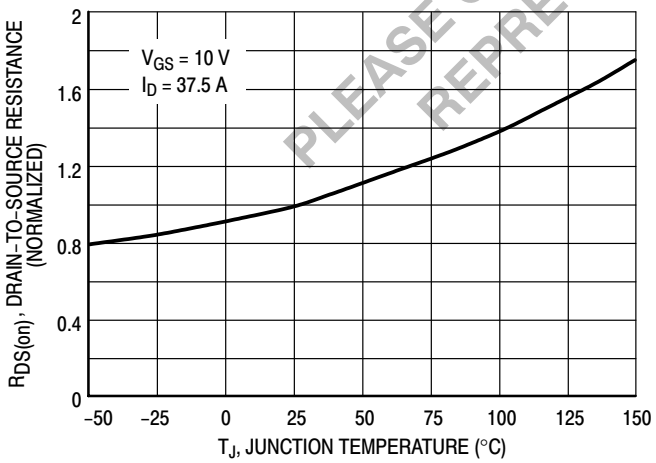



**Figure 5. On−Resistance Variation with Temperature**

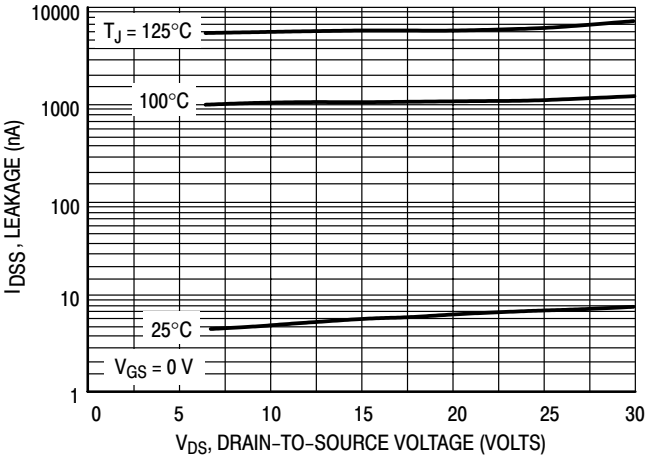



**Figure 6. Drain−To−Source Leakage Current versus Voltage**

## POWER MOSFET SWITCHING

Switching behavior is most easily modeled and predicted by recognizing that the power MOSFET is charge controlled. The lengths of various switching intervals (Δt) are determined by how fast the FET input capacitance can be charged by current from the generator.

The published capacitance data is difficult to use for calculating rise and fall because drain−gate capacitance varies greatly with applied voltage. Accordingly, gate charge data is used. In most cases, a satisfactory estimate of average input current ($I_{G(AV)}$) can be made from a rudimentary analysis of the drive circuit so that

$t = Q/I_{G(AV)}$

During the rise and fall time interval when switching a resistive load, $V_{GS}$ remains virtually constant at a level known as the plateau voltage, $V_{SGP}$. Therefore, rise and fall times may be approximated by the following:

$t_r = Q_2 \times R_G/(V_{GG} - V_{GSP})$
$t_f = Q_2 \times R_G/V_{GSP}$

where

$V_{GG}$ = the gate drive voltage, which varies from zero to $V_{GG}$
$R_G$ = the gate drive resistance
and $Q_2$ and $V_{GSP}$ are read from the gate charge curve.

During the turn−on and turn−off delay times, gate current is not constant. The simplest calculation uses appropriate values from the capacitance curves in a standard equation for voltage change in an RC network. The equations are:

$t_{d(on)} = R_G C_{iss} \ln [V_{GG}/(V_{GG} - V_{GSP})]$
$t_{d(off)} = R_G C_{iss} \ln (V_{GG}/V_{GSP})$

The capacitance ($C_{iss}$) is read from the capacitance curve at a voltage corresponding to the off−state condition when calculating $t_{d(on)}$ and is read at a voltage corresponding to the on−state when calculating $t_{d(off)}$.

At high switching speeds, parasitic circuit elements complicate the analysis. The inductance of the MOSFET source lead, inside the package and in the circuit wiring which is common to both the drain and gate current paths, produces a voltage at the source which reduces the gate drive current. The voltage is determined by Ldi/dt, but since di/dt is a function of drain current, the mathematical solution is complex. The MOSFET output capacitance also complicates the mathematics. And finally, MOSFETs have finite internal gate resistance which effectively adds to the resistance of the driving source, but the internal resistance is difficult to measure and, consequently, is not specified.

The resistive switching time variation versus gate resistance (Figure 9) shows how typical switching performance is affected by the parasitic circuit elements. If the parasitics were not present, the slope of the curves would maintain a value of unity regardless of the switching speed. The circuit used to obtain the data is constructed to minimize common inductance in the drain and gate circuit loops and is believed readily achievable with board mounted components. Most power electronic loads are inductive; the data in the figure is taken with a resistive load, which approximates an optimally snubbed inductive load. Power MOSFETs may be safely operated into an inductive load; however, snubbing reduces switching losses.

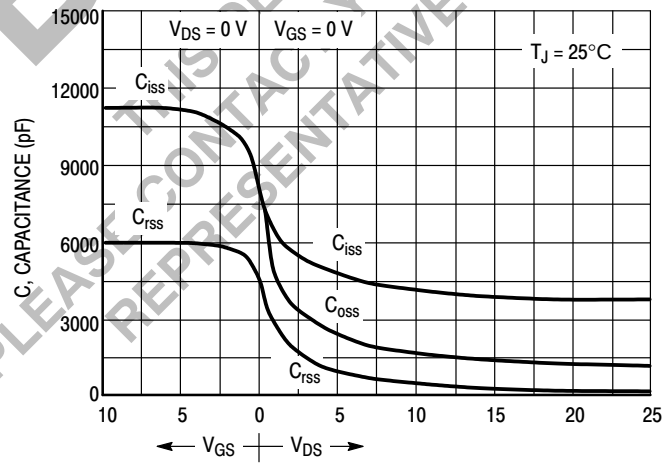



**Figure 7. Capacitance Variation**

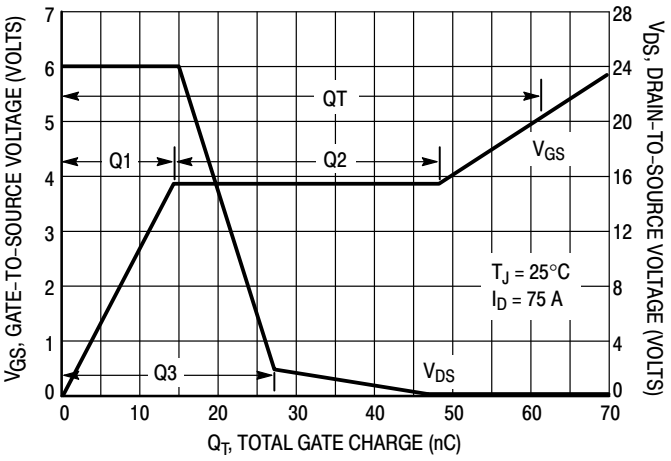



**Figure 8. Gate−To−Source and Drain−To−Source Voltage versus Total Charge**

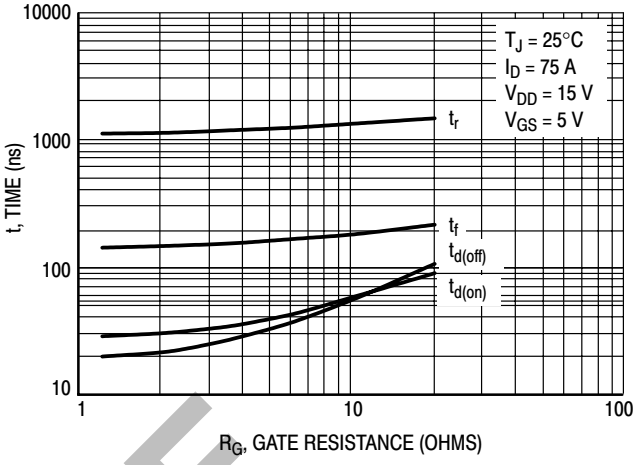



**Figure 9. Resistive Switching Time Variation versus Gate Resistance**

## DRAIN−TO−SOURCE DIODE CHARACTERISTICS

The switching characteristics of a MOSFET body diode are very important in systems using it as a freewheeling or commutating diode. Of particular interest are the reverse recovery characteristics which play a major role in determining switching losses, radiated noise, EMI and RFI.

System switching losses are largely due to the nature of the body diode itself. The body diode is a minority carrier device, therefore it has a finite reverse recovery time, $t_{rr}$, due to the storage of minority carrier charge, $Q_{RR}$, as shown in the typical reverse recovery wave form of Figure 12. It is this stored charge that, when cleared from the diode, passes through a potential and defines an energy loss. Obviously, repeatedly forcing the diode through reverse recovery further increases switching losses. Therefore, one would like a diode with short $t_{rr}$ and low $Q_{RR}$ specifications to minimize these losses.

The abruptness of diode reverse recovery effects the amount of radiated noise, voltage spikes, and current ringing. The mechanisms at work are finite irremovable circuit parasitic inductances and capacitances acted upon by high di/dts. The diode's negative di/dt during $t_a$ is directly controlled by the device clearing the stored charge. However, the positive di/dt during $t_b$ is an uncontrollable diode characteristic and is usually the culprit that induces current ringing. Therefore, when comparing diodes, the ratio of $t_b/t_a$ serves as a good indicator of recovery abruptness and thus gives a comparative estimate of probable noise generated. A ratio of 1 is considered ideal and values less than 0.5 are considered snappy.

Compared to ON Semiconductor standard cell density low voltage MOSFETs, high cell density MOSFET diodes are faster (shorter $t_{rr}$), have less stored charge and a softer reverse recovery characteristic. The softness advantage of the high cell density diode means they can be forced through reverse recovery at a higher di/dt than a standard cell MOSFET diode without increasing the current ringing or the noise generated. In addition, power dissipation incurred from switching the diode will be less due to the shorter recovery time and lower switching losses.



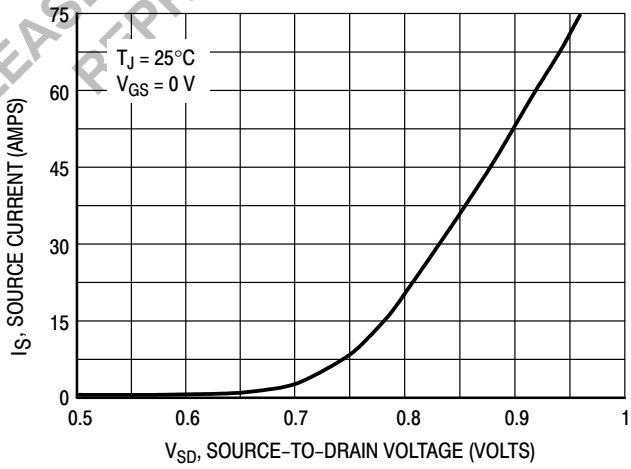



**Figure 10. Diode Forward Voltage versus Current**

## SAFE OPERATING AREA

The Forward Biased Safe Operating Area curves define the maximum simultaneous drain−to−source voltage and drain current that a transistor can handle safely when it is forward biased. Curves are based upon maximum peak junction temperature and a case temperature ($T_C$) of 25°C. Peak repetitive pulsed power limits are determined by using the thermal response data in conjunction with the procedures discussed in AN569, “Transient Thermal Resistance−General Data and Its Use.”

Switching between the off−state and the on−state may traverse any load line provided neither rated peak current ($I_{DM}$) nor rated voltage (VDSS) is exceeded, and that the transition time ($t_r$, $t_f$) does not exceed 10 μs. In addition the total power averaged over a complete switching cycle must not exceed $(T_{J(MAX)} − T_C)/(R_{\theta JC})$.

A power MOSFET designated E−FET can be safely used in switching circuits with unclamped inductive loads. For reliable operation, the stored energy from circuit inductance dissipated in the transistor while in avalanche must be less than the rated limit and must be adjusted for operating conditions differing from those specified. Although industry practice is to rate in terms of energy, avalanche energy capability is not a constant. The energy rating decreases non−linearly with an increase of peak current in avalanche and peak junction temperature.

Although many E−FETs can withstand the stress of drain−to−source avalanche at currents up to rated pulsed current ($I_{DM}$), the energy rating is specified at rated continuous current ($I_D$), in accordance with industry custom. The energy rating must be derated for temperature as shown in the accompanying graph (Figure 13). Maximum energy at currents below rated continuous $I_D$ can safely be assumed to equal the values indicated.

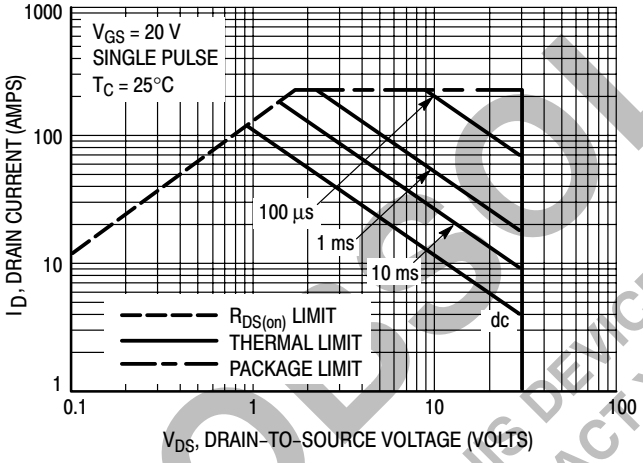



**Figure 11. Maximum Rated Forward Biased Safe Operating Area**

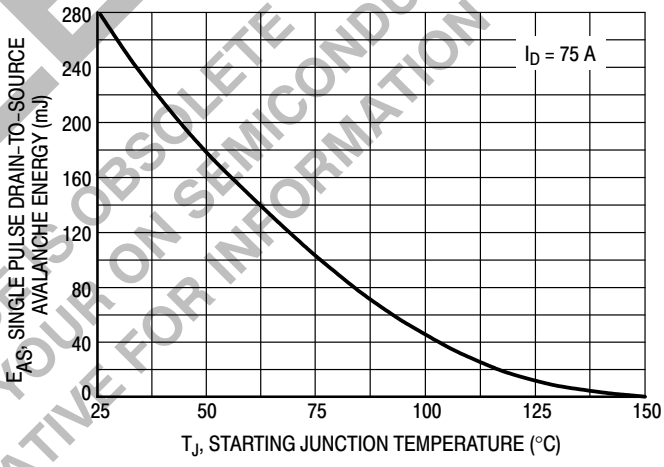



**Figure 12. Maximum Avalanche Energy versus Starting Junction Temperature**

## TYPICAL ELECTRICAL CHARACTERISTICS

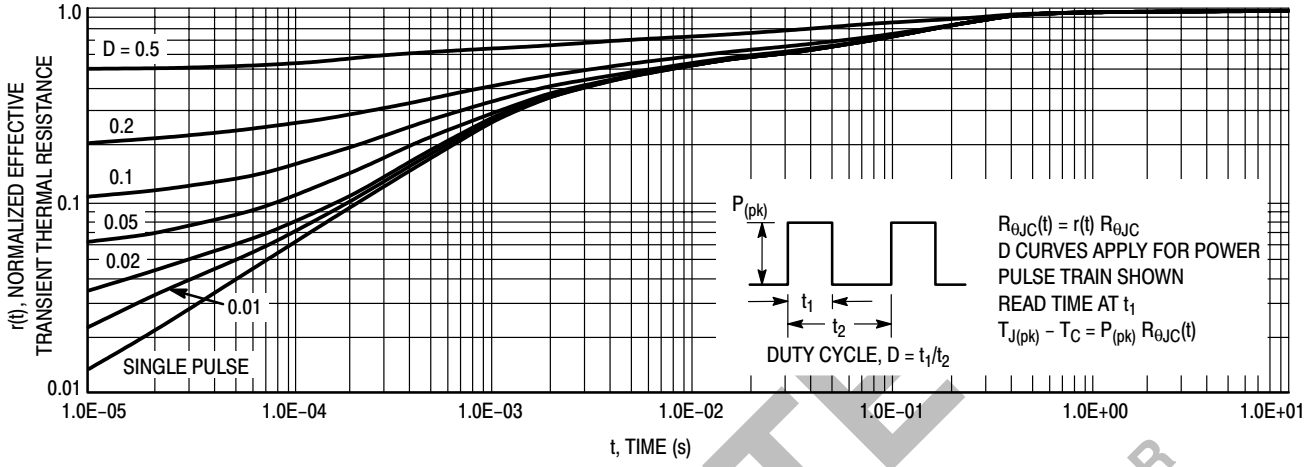



**Figure 13. Thermal Response**

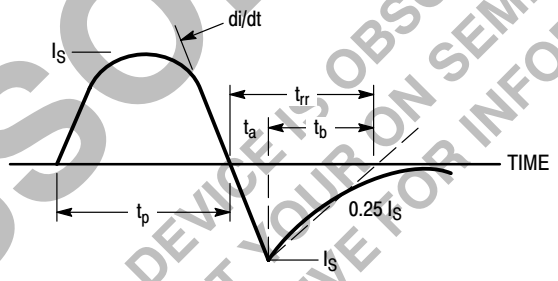
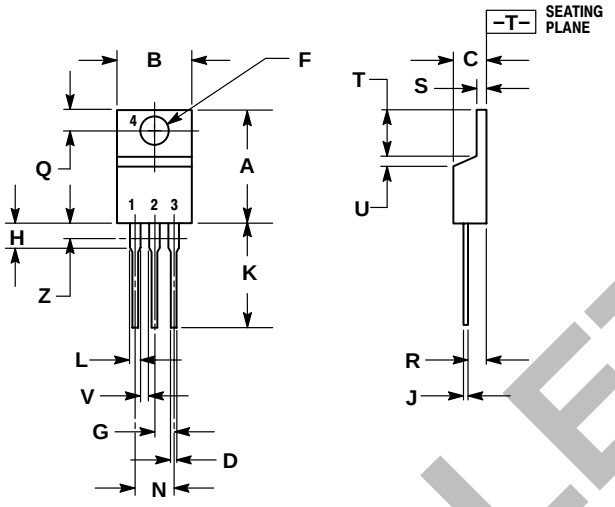



**Figure 14. Diode Reverse Recovery Waveform**

## PACKAGE DIMENSIONS

**TO−220 THREE−LEAD**
**TO−220AB**
CASE 221A−09
ISSUE AA




NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

| | INCHES | | MILLIMETERS | |
|---|---|---|---|---|
| DIM | MIN | MAX | MIN | MAX |
| A | 0.570 | 0.620 | 14.48 | 15.75 |
| B | 0.380 | 0.405 | 9.66 | 10.28 |
| C | 0.160 | 0.190 | 4.07 | 4.82 |
| D | 0.025 | 0.035 | 0.64 | 0.88 |
| F | 0.142 | 0.147 | 3.61 | 3.73 |
| G | 0.095 | 0.105 | 2.42 | 2.66 |
| H | 0.110 | 0.155 | 2.80 | 3.93 |
| J | 0.018 | 0.025 | 0.46 | 0.64 |
| K | 0.500 | 0.562 | 12.70 | 14.27 |
| L | 0.045 | 0.060 | 1.15 | 1.52 |
| N | 0.190 | 0.210 | 4.83 | 5.33 |
| Q | 0.100 | 0.120 | 2.54 | 3.04 |
| R | 0.080 | 0.110 | 2.04 | 2.79 |
| S | 0.045 | 0.055 | 1.15 | 1.39 |
| T | 0.235 | 0.255 | 5.97 | 6.47 |
| U | 0.000 | 0.050 | 0.00 | 1.27 |
| V | 0.045 | --- | 1.15 | --- |
| Z | --- | 0.080 | --- | 2.04 |

STYLE 5:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN





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